

INFRARED RAMAN SCATTERING BY FREE  
HOLES IN UNIAXIALLY COMPRESSED *p*-Ge

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S u m m a r y

Infrared light scattering by free carriers in uniaxially compressed Ge of the *p*-type with concentrations ranging from  $5 \cdot 10^{15}$  to  $3 \cdot 10^{16}$  hole  $\cdot \text{cm}^{-3}$  is investigated. A line is found in the Raman spectra whose spectral position varies as a stress-dependent splitting of topmost valance bands. This line is attributed to the scattering due to hole quadruple moment fluctuations during interband transitions.